

SUPPORT FOR THE AMENDMENTS

The amendment to Claim 13 is supported by the specification, particularly by the Example and page 7, line 2, and by Claim 5. Accordingly, no new matter is believed to have been added to the present application by the amendments submitted above.

REMARKS

Claims 13-17 and 20-30 are now pending. Favorable reconsideration is respectfully requested.

Applicants would like to thank Examiners Zimmer and Bos for the helpful and courteous discussion held with their representative on June 24, 2009. During the discussion, the amendments to Claim 13 were discussed. The following remarks expand on the discussion with the Examiner.

The present invention relates to a process for producing high-purity silicon, comprising thermally decomposing a gas phase mixture comprising monosilane and a monochlorosilane, and depositing silicon,

where the thermal decomposition and deposition are carried out at a temperature in a range from 600 to 1250°C and at a pressure of from 1.2 bar abs. to 5 bar abs. See Claim 13.

As described in the specification, the Inventors have found that operating the process at the specified temperature and pressure provides deposited silicon in high yield with very little production of dust.

The rejection of Claim 13 under 35 U.S.C. §102(b) over JP 2001-064774 (JP '774) is respectfully traversed. As recognized by the Examiner during the personal discussion, JP '775 fails to disclose the temperature and process features specified in Claim 13. Accordingly, withdrawal of this ground of rejection is respectfully requested.

The rejection of Claims 14-17, 20-24, 26-28 and 30 under 35 U.S.C. §103(a) over JP '744 is believed to be moot. The subject matter of Claims 18 and 19 has been incorporated into Claim 13. Since neither of those claims were rejected, the rejection is believed to be moot. Withdrawal of this ground of rejection is respectfully requested.

The rejection of the Claims 13-30 under 35 U.S.C. §103(a) over Flagella '441 in view of JP '774 is respectfully traversed. The cited references fail to suggest the claimed process.

Neither reference alone, or taken on combination, suggests conducting the thermal decomposition and deposition at a temperature in a range from 600 to 1250°C and at a pressure of from 1.2 bar abs. to 5 bar abs., as claimed. In addition, the combination of Flagella '441 and JP '774 fails to suggest that operating the process at the specified temperature and pressure provides deposited silicon in high yield with very little production of dust.

In view of the foregoing, the combination of Flagella '441 and JP '774 fails to suggest the claimed process. Accordingly, the subject matter of Claims 13-17 and 20-30 is not obvious over those references. Withdrawal of this ground of rejection is respectfully requested.

Applicants submit that the present application is in condition for allowance. Early notice to this effect is earnestly solicited.

Respectfully submitted,

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